

2SC495 2SC496

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

MEDIUM POWER AMPLIFIER APPLICATIONS.

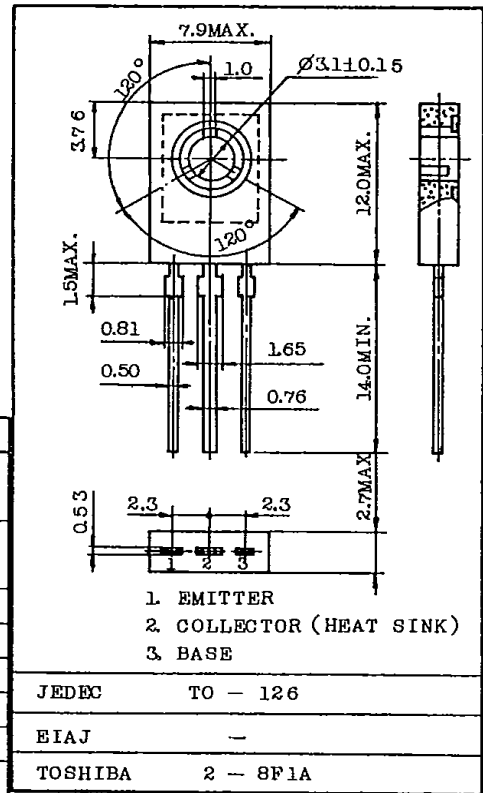
FEATURES:

- Low Collector Saturation Voltage
: $V_{CE(sat)}=0.25V$ (Typ.)
- 0.5 ~ 2 Watts Output Application.
- Complementary to 2SA505 and 2SA496.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	2SC495	70
		2SC496	40
Collector-Emitter Voltage	VCEO	2SC495	50
		2SC496	30
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	1	A
Emitter Current	IE	-1	A
Collector Power Dissipation	PC	1	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55 ~ 150	°C

Unit in mm



JEDEC TO - 186
EIAJ -
TOSHIBA 2 - 8F1A
Mounting Kit No. AC46C
Weight : 0.72g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	ICBO	V _{CB} =30V, I _E =0	-	-	1.0	μA	
Emitter Cut-off Current	IEBO	V _{EB} =5V, I _C =0	-	-	1.0	μA	
Collector-Emitter Breakdown Voltage	V(BR)CEO	I _C =10mA, I _B =0	2SC495	50	-	-	V
			2SC496	30	-	-	
Emitter-Base Breakdown Voltage	V(BR)EBO	I _E =1mA, I _C =0	5	-	-	V	
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =2V, I _C =50mA	40	-	240		
	h _{FE} (2)	V _{CE} =2V, I _C =800mA	13	-	-		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA	-	0.25	0.8	V	
Base-Emitter Voltage	V _{BE}	V _{CE} =2V, I _C =500mA	-	0.9	1.1	V	
Transition Frequency	f _T	V _{CE} =10V, I _C =10mA	50	100	-	MHz	
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	10	-	pF	

Note : h_{FE}(1) Classification R : 40~80, O : 70~140, Y : 120~240

TOSHIBA CORPORATION

